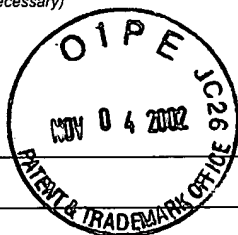


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STATEMENT BY APPLICANT**

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Sheet 1 of 2

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<b>Application Number</b>	09/135413
<b>Filing Date</b>	August 14, 1998
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	2818
<b>Examiner Name</b>	Nguyen, Viet
<b>Attorney Docket No:</b>	00303.354US2

**Viet Q. Nguyen**  
Primary Examiner

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
W	US-3,792,465	02/12/1974	Collins, D. R., et al	340	324 R	12/30/1971
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**Viet Q. Nguyen**  
Primary Examiner

**FOREIGN PATENT DOCUMENTS**

**Viet Q. Nguyen**  
Primary Examiner

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
W	JP-2203564	08/13/1990	Fujii, Y., et al	HO1 L	29/46	
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
W		BELTRAM, F., et al. "GaAlAs/GaAs Floating-Gate Memory Devices with Graded-Gap Injector Grown by Molecular-Beam Epitaxy", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-7, (Dec. 1988), 2451	
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EXAMINER

*V. Nguyen*

DATE CONSIDERED

12/28/02

Substitute Disclosure Statement Form (PTO-1449)

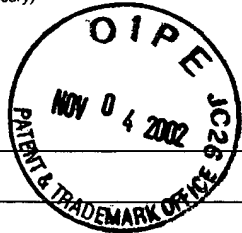
\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Examiner Name	Nguyen, Viet

Sheet 2 of 2

Attorney Docket No: 00303.354US2

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
W		LOTT, J.A., et al., "Charge Storage in InAlAs/InGaAs/InP Floating Gate Heterostructures", <u>Electronics Letters</u> , 26, (July 5, 1990), 972-973	
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Viet Q. Nguyen  
Primary Examiner

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